# **ON Semiconductor**

# Is Now



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# **MPS6729**

**Preferred Device** 

# One Watt Amplifier Transistor

# **PNP Silicon**

#### **Features**

• Pb-Free Package is Available\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	-80	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	-80	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	-4.0	Vdc
Collector Current – Continuous	Ic	-500	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.0 8.0	W mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	2.5 20	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

#### THERMAL CHARACTERISTICS

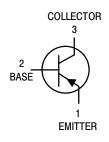
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	50	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



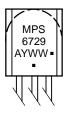
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#### http://onsemi.com





### **MARKING DIAGRAM**



MPS6729 = Device Code A = Assembly Location

Y = Year
WW = Work Week
= Pb-Free Package
(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping
MPS6729	TO-92	5000 Units / Bulk
MPS6729G	TO-92 (Pb-Free)	5000 Units / Bulk

**Preferred** devices are recommended choices for future use and best overall value.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### **MPS6729**

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	·			
Collector – Emitter Breakdown Voltage (Note 1) (I <sub>C</sub> = -1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	-80	-	Vdc
Collector – Base Breakdown Voltage (I <sub>C</sub> = 0.1 mA, I <sub>E</sub> = 0)	V <sub>(BR)</sub> CBO	-80	-	Vdc
Emitter – Base Breakdown Voltage ( $I_E = -10 \mu Adc$ , $I_C = 0$ )	V <sub>(BR)EBO</sub>	-5.0	-	Vdc
Collector Cutoff Current (V <sub>CB</sub> = -60 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	-0.1	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = -5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	-10	μAdc
ON CHARACTERISTICS (Note 1)				
DC Current Gain ( $I_C = -50$ mAdc, $V_{CE} = -1.0$ Vdc) ( $I_C = -250$ mAdc, $V_{CE} = -1.0$ Vdc)	h <sub>FE</sub>	80 50	_ 250	-
Collector – Emitter Saturation Voltage (I <sub>C</sub> = -250 mAdc, I <sub>B</sub> = -10 mAdc)	V <sub>CE(sat)</sub>	-	-0.5	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = -250 mAdc, V <sub>CE</sub> = -1.0 Vdc)	V <sub>BE(on)</sub>	-	-1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS	<u>.</u>			
Collector–Base Capacitance (V <sub>CB</sub> = -10 Vdc, f = 1.0 MHz)	C <sub>cb</sub>	-	30	pF
Small–Signal Current Gain (I <sub>C</sub> = 200 mA, V <sub>CE</sub> = 5.0 V, f = 20 MHz)	h <sub>fe</sub>	2.5	25	

<sup>1.</sup> Pulse Test: Pulse Width  $\leq 300 \,\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

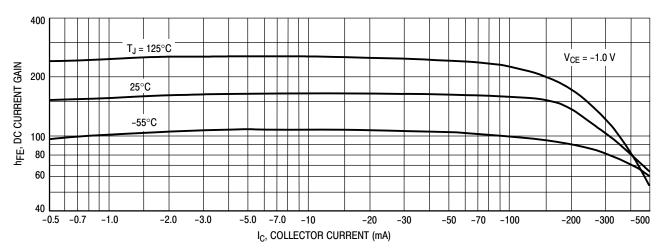


Figure 1. DC Current Gain

# **MPS6729**

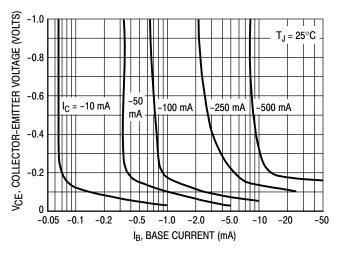


Figure 2. Collector Saturation Region

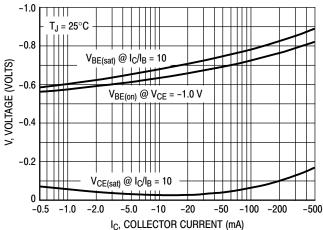


Figure 3. "On" Voltages

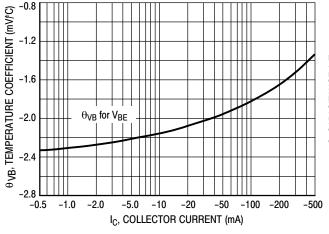


Figure 4. Base-Emitter Temperature Coefficient

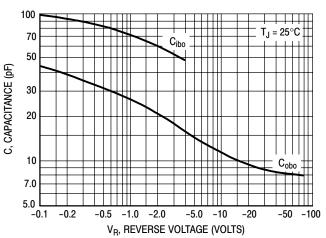


Figure 5. Capacitance

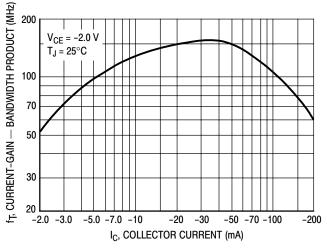


Figure 6. Current-Gain - Bandwidth Product

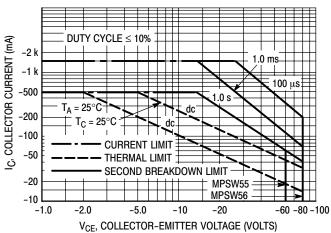
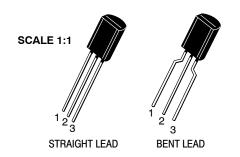


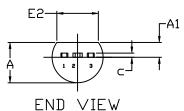
Figure 7. Active Region - Safe Operating Area

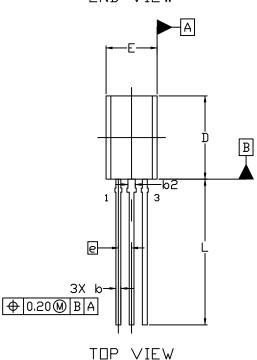


TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

**DATE 05 MAR 2021** 

### STRAIGHT LEAD





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS					
DIM	MIN.	N□M.	MAX.			
Δ	3.75	3.90	4.05			
A1	1.28	1.43	1.58			
Ø	0.38	0.465	0.55			
ρQ	0.62	0.70	0.78			
C	0.35	0.40	0.45			
D	7.85	8.00	8.15			
E	4.75	4.90	5.05			
E2	3.90					
е	1.27 BSC					
L	13.80	14.00	14.20			

### **STYLES AND MARKING ON PAGE 3**

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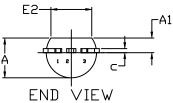
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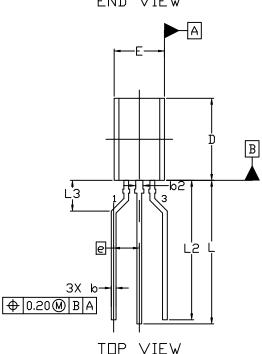


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### FORMED LEAD





#### NOTES:

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	MILLIMETERS					
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A1	1.28	1.43	1.58			
b	0.38	0.465	0.55			
b2	0.62	0.70	0.78			
c	0.35	0.40	0.45			
D	7.85	8.00	8.15			
E	4.75	4.90	5.05			
E2	3.90					
е		2.50 BSC				
L	13.80	14.00	14.20			
L2	13.20	13.60	14.00			
L3	3.00 REF					

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### TO-92 (TO-226) 1 WATT

CASE 29-10 ISSUE D

### **DATE 05 MAR 2021**

STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	PIN 1.	CATHODE CATHODE ANODE		DRAIN SOURCE GATE
	GATE	PIN 1.	SOURCE DRAIN	PIN 1. 2.	DRAIN GATE	STYLE 9: PIN 1. 2. 3.	BASE 1 EMITTER		
2.	CATHODE & ANODE	2.	MAIN TERMINAL 1 GATE MAIN TERMINAL 2	2.	ANODE 1 GATE CATHODE 2	2.	EMITTER		
2.	ANODE	PINI 1	COLLECTOR BASE EMITTER	PIN 1	ANODE	DINI 1		2.	NOT CONNECTED CATHODE ANODE
2.			GATE	PIN 1. 2.	GATE SOURCE DRAIN	PIN 1. 2.	EMITTER COLLECTOR/ANODE CATHODE	PIN 1. 2.	
	V <sub>CC</sub>		MT SUBSTRATE	PIN 1. 2.	CATHODE	PIN 1. 2.		PIN 1. 2.	
		STYLE 32: PIN 1. 2. 3.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN	PIN 1. 2.	INPUT GROUND LOGIC		

# GENERIC MARKING DIAGRAM\*



XXXX = Specific Device Code

A = Assembly Location

L = Wafer Lot Y = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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